



## Unbalanced CMOS Switch for D-band Dicke Imaging System

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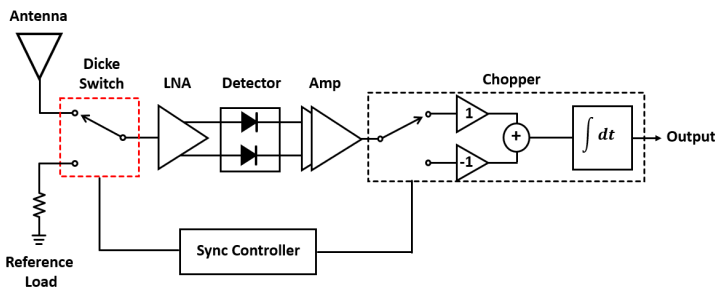


### Background

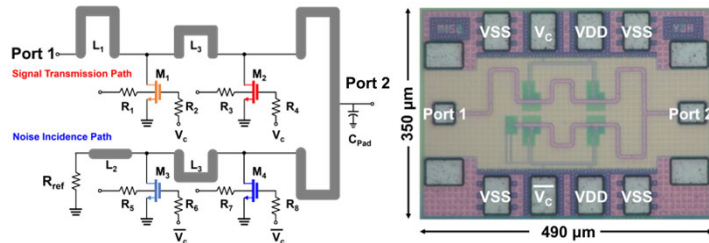
1. Performance of the millimeter-wave imaging systems greatly rely on the sensitivity of the receiver system.
2. A Dicke switch eliminates noise contained in the signal flowing from antenna, providing a high signal-to-noise ratio in the receiver front-end.
3. Previous researches are implemented with rather high-cost technologies, originating from symmetric single-pole double-throw (SPDT) topologies, which cannot overcome the trade-off relationship between insertion loss and isolation characteristics.

### Methods

#### ✓ Millimeter-wave Dicke-radiometer architecture



#### ✓ Proposed Dicke Switch Circuit



#### 1. Shunt transistor size design

→ Modeling the transistors with **on-state resistors** and **off-state capacitors** to determine the **optimum size of transistors**.

#### 2. Priorities of the two paths

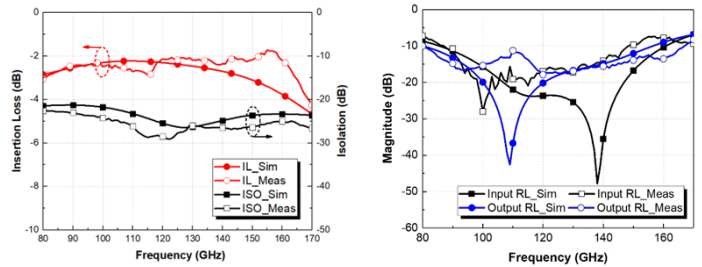
→ **Unbalanced transistors** give the best solution, as each path requires different traits, **alleviating the trade-off relationship**.

#### 3. Impedance mismatch by asymmetric structure

→ **Different lengths of transmission line** are designed to achieve **impedance matching** for the antenna and reference load path.

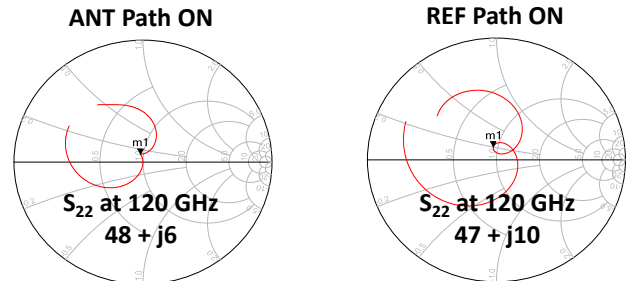
### Results

#### ✓ Measured S-parameter results



Minimum **1.7 dB** Insertion loss & maximum **29 dB** Isolation.

#### ✓ Noise flow analysis for each path



Similar output reflection coefficient corresponding to the control signal.

➔ Noise signal successfully eliminated through the Dicke switch operation.

|                     | This Work      | [1]               | [2]                |
|---------------------|----------------|-------------------|--------------------|
| Technology          | 65-nm CMOS     | 90-nm SiGe BiCMOS | 130-nm SiGe BiCMOS |
| Frequency (GHz)     | 80-150         | 110-170           | 110-170            |
| Isolation (dB)      | <b>22-29</b>   | 20                | 30                 |
| Insertion Loss (dB) | <b>1.7-2.8</b> | 2.5               | 2.6                |

[1] R. Ben Yishay, et al, "D-band Dicke-radiometer in 90 nm SiGe BiCMOS technology," Proc. IEEE MTT-S International Microwave Symposium, Honolulu, HI, USA, Jun. 2017.

[2] B. Cetindogan, et al, "A D-band SPDT switch utilizing reverse-saturated SiGe HBTs for Dicke-radiometers," Proc. 11th German Microwave Conference, Freiburg, Germany, Mar. 2018.

### Conclusion

**Unbalanced topology proves enhanced performance suitable for millimeter-wave Dicke radiometers.**

#### < Acknowledgement >

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